

10758651\_CLS  
Most Frequently Occurring Classifications of Patents Returned  
From A Search of 10758651 on July 28, 2004

Original Classifications

9 250/307  
5 250/311  
4 250/492.21  
2 430/619  
2 438/14

Cross-Reference Classifications

6 250/307  
5 250/309  
5 250/311  
5 250/492.21  
4 216/60  
3 204/192.34  
3 250/306  
3 250/310  
3 250/442.11  
3 250/492.2  
2 204/298.36  
2 216/39  
2 216/66  
2 216/85  
2 250/492.1  
2 250/559.33  
2 438/16  
2 438/706  
2 438/712

Combined Classifications

15 250/307  
10 250/311  
9 250/492.21  
6 250/309  
4 216/60  
4 250/310  
4 250/442.11  
3 204/192.34  
3 250/306  
3 250/492.2  
2 204/298.36  
2 216/33  
2 216/39  
2 216/59  
2 216/66

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2 216/85  
2 219/693  
2 219/745  
2 250/492.1  
2 250/559.33  
2 324/751  
2 428/408  
2 430/619  
2 438/14  
2 438/16  
2 438/706  
2 438/712

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Titles of Most Frequently Occurring Classifications of Patents Returned

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15	250/307	(9 OR, 6 XR)
	Class 250 :	RADIANT ENERGY
	250/306	INSPECTION OF SOLIDS OR LIQUIDS BY CHARGED PARTICLES
	250/307	.Methods
10	250/311	(5 OR, 5 XR)
	Class 250 :	RADIANT ENERGY
	250/306	INSPECTION OF SOLIDS OR LIQUIDS BY CHARGED PARTICLES
	250/311	.Electron microscope type
9	250/492.21	(4 OR, 5 XR)
	Class 250 :	RADIANT ENERGY
	250/492.1	IRRADIATION OF OBJECTS OR MATERIAL
	250/492.2	.Irradiation of semiconductor devices
	250/492.21	..Ion bombardment
6	250/309	(1 OR, 5 XR)
	Class 250 :	RADIANT ENERGY
	250/306	INSPECTION OF SOLIDS OR LIQUIDS BY CHARGED PARTICLES
	250/309	.Positive ion probe or microscope type
4	216/60	(0 OR, 4 XR)
	Class 216 :	ETCHING A SUBSTRATE: PROCESSES
	216/58	GAS PHASE ETCHING OF SUBSTRATE
	216/59	.With measuring, testing, or inspecting
	216/60	..By optical means or of an optical property
4	250/310	(1 OR, 3 XR)
	Class 250 :	RADIANT ENERGY
	250/306	INSPECTION OF SOLIDS OR LIQUIDS BY CHARGED PARTICLES
	250/310	.Electron probe type
4	250/442.11	(1 OR, 3 XR)
	Class 250 :	RADIANT ENERGY
	250/306	INSPECTION OF SOLIDS OR LIQUIDS BY CHARGED PARTICLES
	250/440.11	.Analyte supports
	250/442.11	..With object moving or positioning means

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3 204/192.34 (0 OR, 3 XR)  
 Class 204 : CHEMISTRY: ELECTRICAL AND WAVE ENERGY  
 204/192.1 .Coating, forming or etching by sputtering  
 204/192.32 ..Sputter etching  
 204/192.34 ...Ion beam etching (e.g., ion milling, etc.)

3 250/306 (0 OR, 3 XR)  
 Class 250 : RADIANT ENERGY  
 250/306 INSPECTION OF SOLIDS OR LIQUIDS BY CHARGED PARTICLES

3 250/492.2 (0 OR, 3 XR)  
 Class 250 : RADIANT ENERGY  
 250/492.1 IRRADIATION OF OBJECTS OR MATERIAL  
 250/492.2 .Irradiation of semiconductor devices

2 204/298.36 (0 OR, 2 XR)  
 Class 204 : CHEMISTRY: ELECTRICAL AND WAVE ENERGY  
 204/193 APPARATUS  
 204/298.01 .Coating, forming or etching by sputtering  
 204/298.31 ..Etching  
 204/298.36 ...Beam or directed flux etching (e.g., ion beam, etc.)

2 216/33 (1 OR, 1 XR)  
 Class 216 : ETCHING A SUBSTRATE: PROCESSES  
 216/33 ADHESIVE OR AUTOGENOUS BONDING OF TWO OR MORE SELF-SUSTAINING PREFORMS WHEREIN AT LEAST T

WO OF THE

G.,

PREFORMS ARE NOT INTENDED TO BE REMOVED (E.  
 PREFABRICATED BASE, ETC.)

2 216/39 (0 OR, 2 XR)  
 Class 216 : ETCHING A SUBSTRATE: PROCESSES  
 216/39 FORMING GROOVE OR HOLE IN A SUBSTRATE WHICH IS SUBSEQUENTLY FILLED OR COATED

2 216/59 (1 OR, 1 XR)  
 Class 216 : ETCHING A SUBSTRATE: PROCESSES  
 216/58 GAS PHASE ETCHING OF SUBSTRATE  
 216/59 .With measuring, testing, or inspecting

2 216/66 (0 OR, 2 XR)  
 Class 216 : ETCHING A SUBSTRATE: PROCESSES  
 216/58 GAS PHASE ETCHING OF SUBSTRATE  
 216/63 .Application of energy to the gaseous etchant

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t 216/66 or to the substrate being etched  
..Using ion beam, ultraviolet, or visible light

2 216/85 (0 OR, 2 XR)

Class 216 : ETCHING A SUBSTRATE: PROCESSES  
216/83 NONGASEOUS PHASE ETCHING OF SUBSTRATE  
216/84 .With measuring, testing, or inspecting  
216/85 ..By optical means or of an optical property

2 219/693 (1 OR, 1 XR)

Class 219 : ELECTRIC HEATING  
219/678 MICROWAVE HEATING  
219/690 .Waveguide applicator  
219/691 ..Slotted  
219/693 ...Having load passage

2 219/745 (1 OR, 1 XR)

Class 219 : ELECTRIC HEATING  
219/678 MICROWAVE HEATING  
219/745 .Field modification

2 250/492.1 (0 OR, 2 XR)

Class 250 : RADIANT ENERGY  
250/492.1 IRRADIATION OF OBJECTS OR MATERIAL

2 250/559.33 (0 OR, 2 XR)

Class 250 : RADIANT ENERGY  
250/200 PHOTOCELLS; CIRCUITS AND APPARATUS  
250/559.01 .With circuit for evaluating a web, strand,  
strip, or sheet  
250/559.29 ..Measuring position  
250/559.33 ...With robotics

2 324/751 (1 OR, 1 XR)

Class 324 : ELECTRICITY: MEASURING AND TESTING  
324/500 FAULT DETECTING IN ELECTRIC CIRCUITS AND OF  
ELECTRIC COMPONENTS  
324/537 .Of individual circuit component or element  
324/750 ..System sensing fields adjacent device under  
test (DUT)  
324/751- - - - - ..Using electron beam probe

2 428/408 (1 OR, 1 XR)

Class 428 : STOCK MATERIAL OR MISCELLANEOUS ARTICLES  
428/408 SELF-SUSTAINING CARBON MASS OR LAYER WITH  
IMPREGNANT OR OTHER LAYER

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2  430/619      (2 OR, 0 XR)
      Class 430 : RADIATION IMAGERY CHEMISTRY: PROCESS,
                  COMPOSITION, OR PRODUCT THEREOF
      430/495.1 RADIATION SENSITIVE PRODUCT
      430/564   .Silver compound sensitizer containing
      430/617   ..Silver compound other than halide, per se, o
r
                  composition for thermographic process pro
cess
      430/618   ...Organic silver compound containing
      430/619   ....And inorganic silver compound

2  438/14       (2 OR, 0 XR)
      Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
      438/14    WITH MEASURING OR TESTING

2  438/16       (0 OR, 2 XR)
      Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
      438/14    WITH MEASURING OR TESTING
      438/16    .Optical characteristic sensed

2  438/706      (0 OR, 2 XR)
      Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
      438/689   CHEMICAL ETCHING
      438/706   .Vapor phase etching (i.e., dry etching)

2  438/712      (0 OR, 2 XR)
      Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
      438/689   CHEMICAL ETCHING
      438/706   .Vapor phase etching (i.e., dry etching)
      438/707   ..Utilizing electromagnetic or wave energy
      438/710   ...By creating electric field (e.g., plasma,
                  glow discharge, etc.)
      438/712   ....Reactive ion beam etching (i.e., RIBE)

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